

ABSTRACT OF THE DISCLOSURE

A manufacturing method for a semiconductor device includes a hole portion formation step for forming hole portions whose entire width is substantially identical to the width of the opening portion in a part of the active surface side of the substrate on which electronic components are formed, a curved surface formation step for curving the bottom surface of the hole portion while maintaining the width of the bottom surface in the hole portions substantially identical to the width of the opening portion, a connecting terminal formation step for forming connecting terminals that serve as the external electrodes of the electronic circuits by burying metal in the hole portions, and an exposure step for exposing a part of the connecting terminals by carrying out processing on the back surface of the substrate.